December 2000

FDD6680S

30V N-Channel PowerTrench® SyncFET™

General Description

The FDD6680S is designed to replace a single MOSFET and Schottky diode in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low $R_{DS(ON)}$ and low gate charge. The FDD6680S includes an integrated Schottky diode using Fairchild's monolithic SyncFET technology. The performance of the FDD6680S as the low-side switch in a synchronous rectifier is indistinguishable from the performance of the FDD6680A in parallel with a Schottky diode.

Applications

- DC/DC converter
- Motor Drives

Features

- 55 A, 30 V $R_{DS(ON)}$ = 11 mΩ @ V_{GS} = 10 V
  $R_{DS(ON)}$ = 17 mΩ @ V_{GS} = 4.5 V
- Includes SyncFET Schottky body diode
- Low gate charge (17nC typical)
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability

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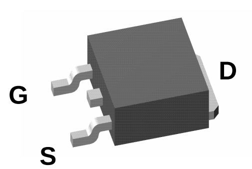

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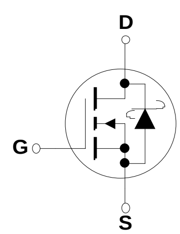


Absolute Maximum Ratings

T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Drain Current – Continuous	(Note 3)	55	A
	– Pulsed	(Note 1a)	100	
P_D	Power Dissipation	(Note 1)	60	W
		(Note 1a)	3.1	
		(Note 1b)	1.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	2.1	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	40	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1b)	96	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDD6680S	FDD6680S	13''	16mm	2500 units

Electrical Characteristics

$T_A = 25°C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain-Source Avalanche Ratings (Note 2)						
W_{DSS}	Drain-Source Avalanche Energy	Single Pulse, $V_{DD} = 15$ V, I_D=14A			245	mJ
I_{AR}	Drain-Source Avalanche Current				14	A
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0$ V, $I_D = 1$ mA	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 1$ mA, Referenced to 25°C		19		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24$ V, $V_{GS} = 0$ V			500	µA
I_{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 20$ V, $V_{DS} = 0$ V			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = –20$ V, $V_{DS} = 0$ V			–100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 1$ mA	1	2	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 1$ mA, Referenced to 25°C		–3.3		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 10$ V, $I_D = 12.5$ A $V_{GS} = 4.5$ V, $I_D = 10$ A V_{GS}= 10 V, I_D = 12.5A, T_J= 125°C		9.5 13.5 17	11 17 23	mΩ
$I_{D(on)}$	On–State Drain Current	$V_{GS} = 10$ V, $V_{DS} = 5$ V	50			A
g_{FS}	Forward Transconductance	$V_{DS} = 15$ V, $I_D = 12.5$ A		27		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 15$ V, $V_{GS} = 0$ V, f = 1.0 MHz		2010		pF
C_{oss}	Output Capacitance			526		pF
C_{rss}	Reverse Transfer Capacitance			186		pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	$V_{DS} = 15$ V, $I_D = 1$ A, $V_{GS} = 10$ V, $R_{GEN} = 6$ Ω		10	18	ns
t_r	Turn–On Rise Time			10	18	ns
$t_{d(off)}$	Turn–Off Delay Time			34	55	ns
t_f	Turn–Off Fall Time			14	23	ns
Q_g	Total Gate Charge	$V_{DS} = 15$ V, $I_D = 12.5$ A, $V_{GS} = 5$ V		17	24	nC
Q_{gs}	Gate–Source Charge			6.2		nC
Q_{gd}	Gate–Drain Charge			5.5		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				4.4	A
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0$ V, $I_S = 4.4$ A (Note 2) $V_{GS} = 0$ V, $I_S = 7$ A (Note 2)		0.49 0.56	0.7	V
t_{rr}	Diode Reverse Recovery Time	I_F = 12.5A, d_{iF}/d_t = 300 A/µs (Note 3)		20		nS
Q_{rr}	Diode Reverse Recovery Charge			19.7		nC

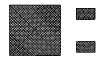
Electrical Characteristics

T_A = 25°C unless otherwise noted

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a) $R_{\theta JA}$ = 40°C/W when mounted on a 1in^2 pad of 2 oz copper



b) $R_{\theta JA}$ = 96°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

3. Maximum current is calculated as: $\sqrt{\dfrac{P_D}{R_{DS(ON)}}}$

where P_D is maximum power dissipation at T_C = 25°C and $R_{DS(on)}$ is at $T_{J(max)}$ and V_{GS} = 10V. Package current limitation is 21A

Typical Characteristics

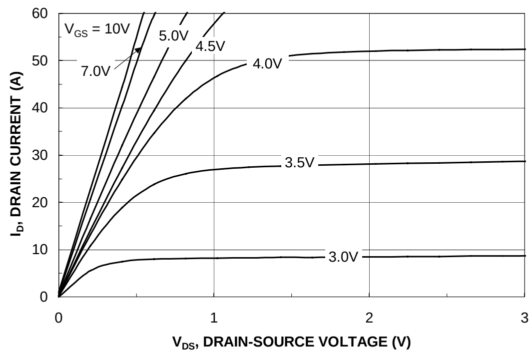


Figure 1. On-Region Characteristics.

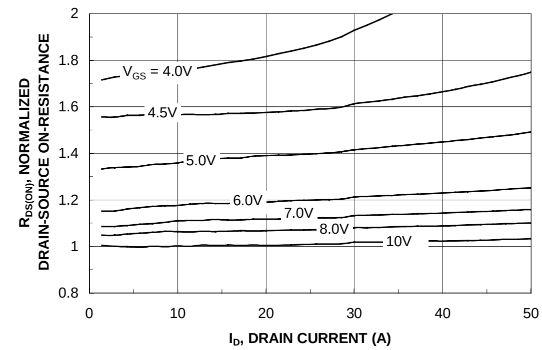


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

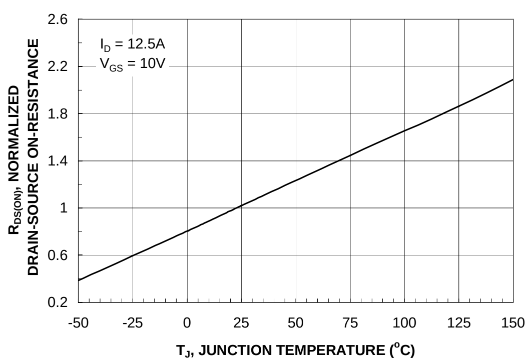


Figure 3. On-Resistance Variation with Temperature.

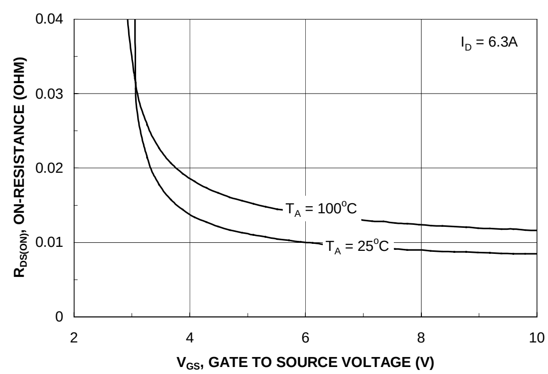


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

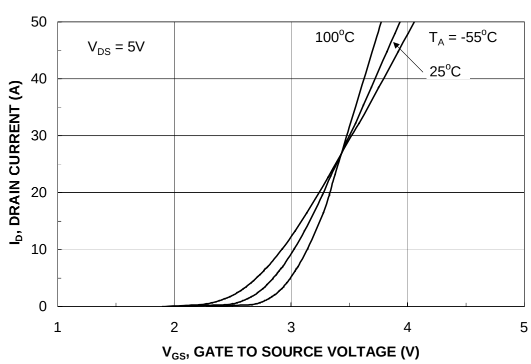


Figure 5. Transfer Characteristics.

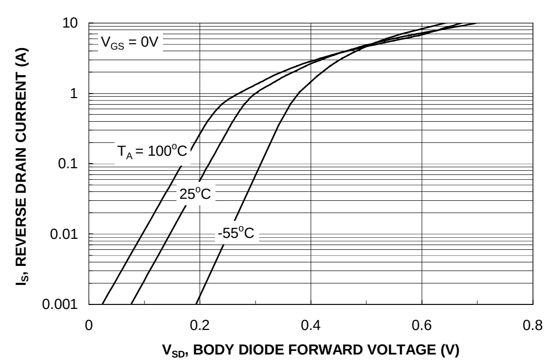


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

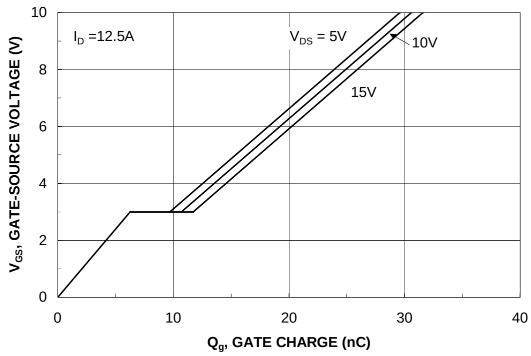


Figure 7. Gate Charge Characteristics.

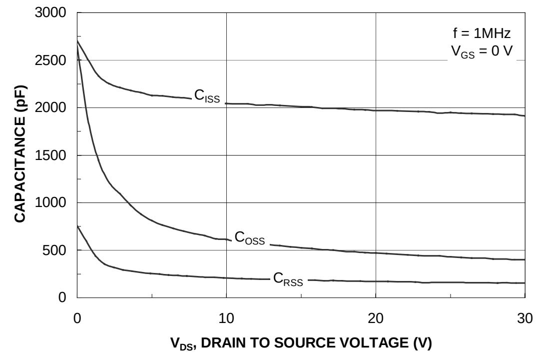


Figure 8. Capacitance Characteristics.

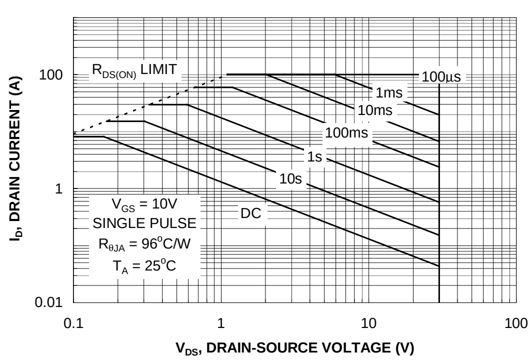


Figure 9. Maximum Safe Operating Area.

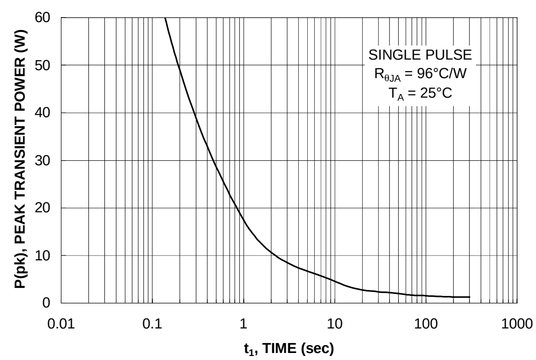


Figure 10. Single Pulse Maximum Power Dissipation.

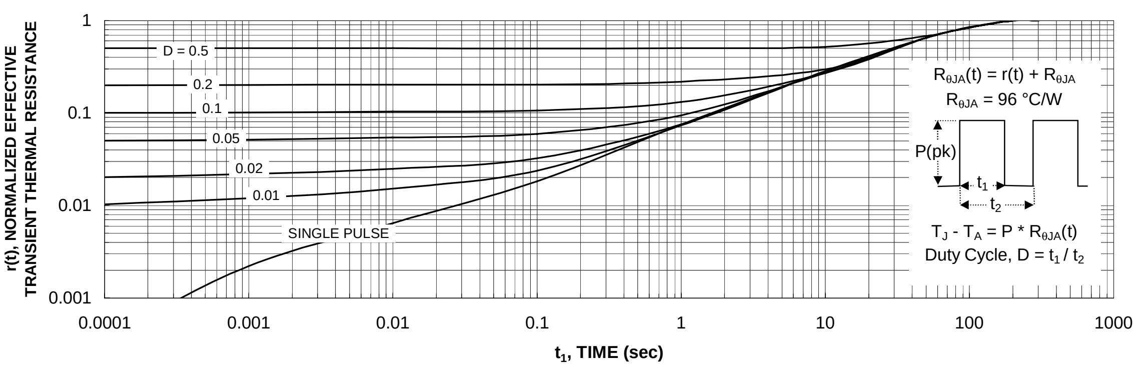


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

Typical Characteristics (continued)

SyncFET Schottky Body Diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 12 shows the reverse recovery characteristic of the FDD6680S.

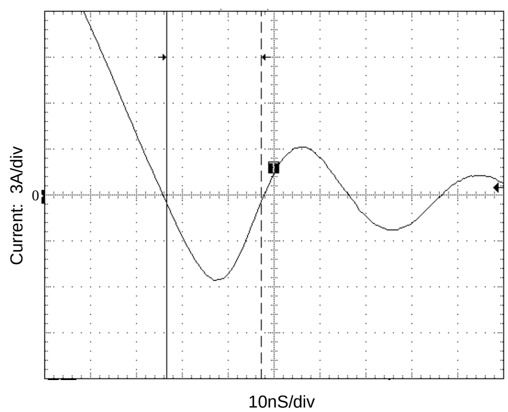


Figure 12. FDD6680S SyncFET body diode reverse recovery characteristic.

For comparison purposes, Figure 13 shows the reverse recovery characteristics of the body diode of an equivalent size MOSFET produced without SyncFET (FDD6680).

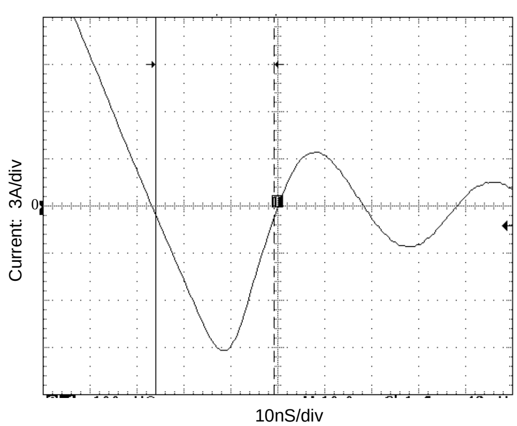


Figure 13. Non-SyncFET (FDS6680) body diode reverse recovery characteristic.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

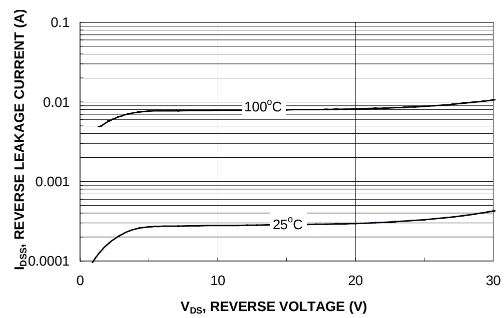


Figure 14. SyncFET body diode reverse leakage versus drain-source voltage and temperature.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.